#a IDS 11-28-01 retake

INFORMATION DISCLOSURE STATEMENT

1-2. Unidirectional thermal evaporation is mentioned in a first article entitled "Facet-Coating Effects on the 1.3 um Strained Multiple-Quantum-Well AlGaInAs/InP Laser Diodes," by Chia-Chien Lin et al., published in the *Japanese Journal of Applied Physics*, Vol. 37 (1998), pp. 6399-6402 and in an article entitled "InGaAs/InP quantum well lasers with sub-mA threshold current," by H. Temkin et al., published in the *Applied Physics Letters*, Vol. 57, No. 16, October 15, 1990. These articles do not disclose the method and devices of the present invention.

3-5. An E-beam process is disclosed in a first article entitled "Edge-Emitting Lasers with Short-Period Semiconductor/Air Distributed Bragg Reflector Mirrors," by Y. Yuan et al., published in the *IEEE Photonics Thechnology Letters*, Vol. 9, No. 7, pp. 881-883, July 1997, a second article entitled "Edge-Emitting GaInAs-AlGaAs Microlasers," by E. Hofling et al., published in *IEEE Photonics Technology Letters*, Vol. 11, No. 8, pp. 943-945, August 1999, and a third article entitled "Continuous Wave Operation of 1.55 um GaInAsP/InP Laser with Semiconductor/Benzocyclobutene Distributed Bragg Reflector," by Mothi Madhan et al., published in the *Japanese Journal of Applied Physics*, Vol. 38, pp. L1240-L1242, November 1, 1999. The third article provides details on filling air gaps with a dielectric. None of these articles disclose the method or devices of the present invention.